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(54) **Title:** METHODS FOR DETERMINING SUITABILITY OF CZOCHRALSKI GROWTH CONDITIONS FOR PRODUCING SUBSTRATES FOR EPITAXY

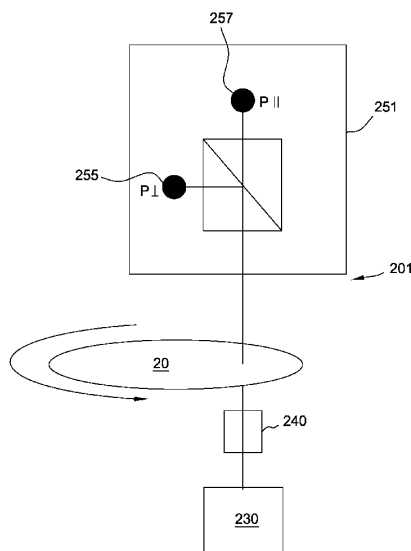


FIG. 15

(57) **Abstract:** Methods for determining suitability of Czochralski growth conditions to produce silicon substrates for epitaxy. The methods involve evaluating substrates sliced from ingots grown under different growth conditions (e.g., impurity profiles) by imaging the wafer by infrared depolarization. An infrared depolarization parameter is generated for each epitaxial wafer. The parameters may be compared to determine which growth conditions are well-suited to produce substrates for epitaxial and/or post-epi heat treatments.

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